

**HYUNDAI**

**HY534256 Series**  
256K x 4-bit CMOS DRAM

**DESCRIPTION**

The HY534256 is the new generation and fast dynamic RAM organized 262,144 x 4-bits. The HY534256 utilizes Hyundai's CMOS silicon gate process technology as well as advanced circuit techniques to provide wide operating margins to the users. Multiplexed address inputs permit the HY534256 to be packaged in a standard 300mil 20 pin PDIP and 20/26 pin SOJ.

The package size provides high system bit densities and is compatible with widely available automated testing and insertion equipments. System oriented feature includes single power supply of 5V± 10% tolerance and direct interfacing capability with high performance logic families such as Schottky TTL.

**FEATURES**

- Low power dissipation  
Max. CMOS standby 5.5mW  
Max. TTL standby 11.0mW  
Max. operating

Speed	Power
60	495mW
70	440mW
80	385mW

- Single power supply of 5V± 10%
- TTL compatible inputs and outputs
- Fast access Time

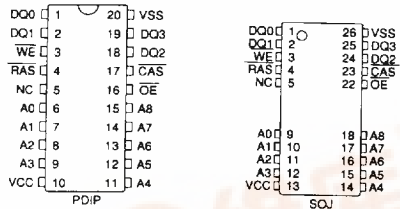
Speed	tRAC	tCAC	tPC
60	60ns	20ns	40ns
70	70ns	20ns	40ns
80	80ns	20ns	45ns

- Fast page mode operation
- Read-Modify-Write capability
- CAS-before-RAS, RAS-only, Hidden refresh
- 512 refresh cycles / 8ms

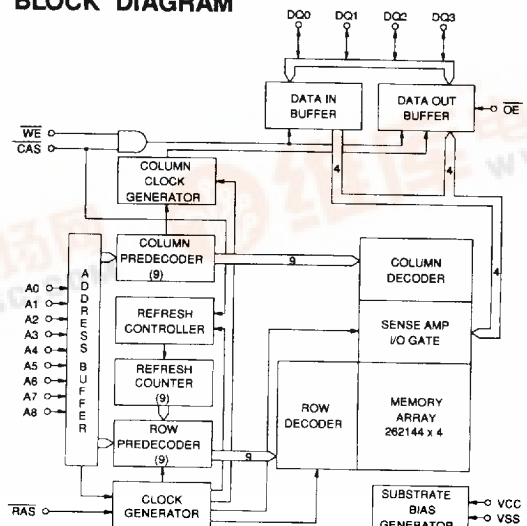
**PIN DESCRIPTION**

RAS	Row Address Strobe
CAS	Column Address Strobe
WE	Write Enable
OE	Output Enable
A0-A8	Address Input
DQ0-DQ3	Data Input/Output
VCC	Power (+ 5V)
Vss	Ground

**PIN CONNECTION**



**BLOCK DIAGRAM**



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1A03-30-MA Y94

46250AA 0002340 845

**ABSOLUTE MAXIMUM RATINGS**

SYMBOL	PARAMETER	RATING	UNIT
TA	Ambient Temperature	0 to 70	°C
TSTG	Storage Temperature	-55 to 150	°C
VIN, VOUT	Voltage on Any Pin Relative to VSS	-1.0 to 7.0	V
VCC	Voltage on VCC Relative to VSS	-1.0 to 7.0	V
Ios	Short Circuit Output Current	50	mA
Pd	Power Dissipation	0.60	W
TSOLDER	Soldering Temperature•Time	260•10	°C•sec

NOTE : Operation at or above Absolute Maximum Ratings can adversely affect device reliability.

**RECOMMENDED DC OPERATING CONDITIONS**

(TA= 0°C to 70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
VCC	Supply Voltage	4.5	5.0	5.5	V
VIH	Input High Voltage	2.4	-	VCC+ 1.0	V
VIL	Input Low Voltage	-1.0	-	0.8	V

NOTE : All voltages are referenced to VSS.



**DC CHARACTERISTICS**

(TA= 0°C to 70°C, VCC= 5V± 10%, VSS= 0V, unless otherwise noted.)

SYMBOL	PARAMETER	TEST CONDITIONS	SPEED	MIN.	MAX.	UNIT	NOTE
ILI	Input Leakage Current (Any Input Pins)	VSS ≤ VIN ≤ VCC All other pins not under test = VSS		-10	10	μA	
ILO	Output Leakage Current (High Impedance State)	VSS ≤ VOUT ≤ VCC RAS & CAS at VIH		-10	10	μA	
ICC1	VCC Supply Current, Operating	tRC = tRC (min.)	60 70 80	- - -	90 80 70	mA	1,2,3
ICC2	VCC Supply Current, TTL Standby	RAS & CAS at VIH, other inputs ≥ VSS		-	2	mA	
ICC3	VCC Supply Current, RAS-only refresh	tRC = tRC (min.)	60 70 80	- - -	90 80 70	mA	1,3
ICC4	VCC Supply Current, Fast Page mode	tPC = tPC (min.)	60 70 80	- - -	70 60 50	mA	1,2,3
ICC5	VCC Supply Current, CMOS Standby	RAS & CAS ≥ VCC-0.2V		-	1	mA	
ICC6	VCC Supply Current, CAS-before-RAS refresh	tRC = tRC (min.)	60 70 80	- - -	90 80 70	mA	1,3
VOL	Output Low Voltage	IOL = 4.2mA		-	0.4	V	
VOH	Output High Voltage	IOH = -5mA		2.4	-	V	

**NOTE :**

1. ICC1, ICC3, ICC4 and ICC6 depend on cycle rate.
2. ICC1 and ICC4 depend on output loading. Specified values are obtained with the output open.
3. It depends on user whether column address is changed or not at least once while RAS = VIL and CAS = VIH.



**AC CHARACTERISTICS**

(TA= 0°C to 70 C, VCC= 5V± 10%, VSS= 0V, unless otherwise noted.) NOTE : 1, 2, 3

#	SYMBOL	PARAMETER	HY534256B/J						UNIT	NOTE
			-60		-70		-80			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
1	tRC	Random Read or Write Cycle Time	120	-	130	-	150	-	ns	
2	tRWC	Read-Modify-Write Cycle Time	175	-	185	-	205	-	ns	
3	tPC	Fast Page Mode Cycle Time	40	-	40	-	45	-	ns	
4	tPRWC	Fast Page Mode Read-Modify-Write Cycle Time	95	-	95	-	100	-	ns	
5	tRAC	Access Time from RAS	-	60	-	70	-	80	ns	4,9,10
6	tCAC	Access Time from CAS	-	20	-	20	-	20	ns	4,9
7	tAA	Access Time from Column Address	-	30	-	35	-	40	ns	4,10
8	tCPA	Access Time from CAS Precharge	-	35	-	35	-	40	ns	4
9	tCLZ	CAS to Output Low Impedance	0	-	0	-	0	-	ns	4
10	tOFF	Output Buffer Turn-off Delay	0	20	0	20	0	20	ns	5
11	tT	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	3
12	tRP	RAS Precharge Time	50	-	50	-	60	-	ns	
13	tRAS	RAS Pulse Width	60	10K	70	10K	80	10K	ns	
14	tRASP	RAS Pulse Width (Fast Page Mode)	60	100K	70	100K	80	100K	ns	
15	tRSH	RAS Hold Time	20	-	20	-	20	-	ns	
16	tCSH	CAS Hold Time	60	-	70	-	80	-	ns	
17	tCAS	CAS Pulse Width	20	10K	20	10K	20	10K	ns	
18	tRCD	RAS to CAS Delay	20	40	20	50	20	60	ns	9
19	tRAD	RAS to Column Address Delay Time	15	30	15	35	15	40	ns	10
20	tCRP	CAS to RAS Precharge Time	5	-	5	-	5	-	ns	
21	tCP	CAS Precharge Time	10	-	10	-	10	-	ns	
22	tASR	Row Address Set-up Time	0	-	0	-	0	-	ns	
23	tRAH	Row Address Hold Time	10	-	10	-	10	-	ns	
24	tASC	Column Address Set-up Time	0	-	0	-	0	-	ns	
25	tCAH	Column Address Hold Time	15	-	15	-	15	-	ns	
26	tAR	Column Address Hold Time from RAS	50	-	55	-	60	-	ns	
27	tRAL	Column Address to RAS Lead Time	30	-	35	-	40	-	ns	
28	tRCS	Read Command Set-up Time	0	-	0	-	0	-	ns	
29	tRCH	Read Command Hold Time Referenced to CAS	0	-	0	-	0	-	ns	6
30	tRRH	Read Command Hold Time Referenced to RAS	0	-	0	-	0	-	ns	6
31	tWCH	Write Command Hold Time	15	-	15	-	15	-	ns	
32	tWCR	Write Command Hold Time from RAS	50	-	55	-	60	-	ns	
33	tWP	Write Command Pulse Width	15	-	15	-	15	-	ns	
34	tRWL	Write Command to RAS Lead Time	20	-	20	-	20	-	ns	
35	tCWL	Write Command to CAS Lead Time	20	-	20	-	20	-	ns	
36	tDS	Data-In Set-up Time	0	-	0	-	0	-	ns	7
37	tDH	Data-In Hold Time	15	-	15	-	15	-	ns	7
38	tDHR	Data-In Hold Time Referenced to RAS	45	-	50	-	55	-	ns	
39	tREF	Refresh Period (512 cycles)	-	8	-	8	-	8	ms	
40	tWCS	Write Command Set-up Time	0	-	0	-	0	-	ns	8



**AC CHARACTERISTICS**

(continued)

#	SYMBOL	PARAMETER	HY534256S/J						UNIT	NOTE
			-60		-70		-80			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
41	tCWD	CAS to WE Delay Time	50	-	50	-	50	-	ns	8
42	tRWD	RAS to WE Delay Time	90	-	100	-	110	-	ns	8
43	tAWD	Column Address to WE Delay Time	60	-	65	-	70	-	ns	8
44	tCSR	CAS Set-up Time (CBR Cycle)	5	-	5	-	5	-	ns	
45	tCHR	CAS Hold Time (CBR Cycle)	15	-	15	-	15	-	ns	
46	tRPC	RAS to CAS Precharge Time	0	-	0	-	0	-	ns	
47	tCPT	CAS Precharge Time (CBR Counter Test)	40	-	40	-	40	-	ns	
48	tROH	RAS Hold Time Reference to OE	10	-	10	-	15	-	ns	
49	tOEA	OE Access Time	-	20	-	20	-	20	ns	
50	tOED	OE to Data Delay	20	-	20	-	20	-	ns	
51	tOEZ	Output Buffer Turn Off Delay Time from OE	0	20	0	20	0	20	ns	5
52	tOEH	OE Command Hold Time	20	-	20	-	20	-	ns	
53	tCPWD	WE Delay Time from CAS Precharge	60	-	65	-	70	-	ns	8
54	tRHCP	RAS Hold Time from CAS Precharge	30	-	35	-	35	-	ns	



**NOTE :**

1. An initial pause of 200 $\mu$ s is required after power-up followed by 8 RAS cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 CAS-before-RAS initialization cycles instead of 8 RAS cycles are required.
2. AC measurements assume  $t_T = 5$ ns.
3.  $V_{IH}(\text{min.})$  and  $V_{IL}(\text{max.})$  are reference levels for measuring timing of input signals. Also, transition times are measured between  $V_{IH}$  and  $V_{IL}$ .
4. Measured with a load equivalent to 2 TTL loads and 100pF.
5.  $t_{OFF}(\text{max.})$  and  $t_{OEZ}$  define the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
6. Either  $t_{RCH}$  or  $t_{RRH}$  must be satisfied for a read cycle.
7. These parameters are referenced to CAS leading edge in early write cycles and to WE leading edge in Read-Modify-Write cycles.
8.  $t_{WCS}$ ,  $t_{RWD}$ ,  $t_{CWD}$ ,  $t_{AWD}$  and  $t_{CPWD}$  are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If  $t_{WCS} \geq t_{WCS}(\text{min.})$ , the cycle is an early write cycle and data out pin will remain open circuit (high impedance) through the entire cycle. If  $t_{RWD} \geq t_{RWD}(\text{min.})$ ,  $t_{CWD} \geq t_{CWD}(\text{min.})$ ,  $t_{AWD} \geq t_{AWD}(\text{min.})$ , and  $t_{CPWD} \geq t_{CPWD}(\text{min.})$ , the cycle is a Read-Modify-Write cycle and data out will contain data read from the selected cell. If neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminated.
9. Operation within the  $t_{RCD}(\text{max.})$  limit insures that  $t_{RAC}(\text{max.})$  can be met.  $t_{RCD}(\text{max.})$  is specified as a reference point only. If  $t_{RCD}$  is greater than the specified  $t_{RCD}(\text{max.})$  limit, then access time is controlled by  $t_{CAC}$ .
10. Operation within the  $t_{RAD}(\text{max.})$  limit insures that  $t_{RAC}(\text{max.})$  can be met.  $t_{RAD}(\text{max.})$  is specified as a reference point only. If  $t_{RAD}$  is greater than the specified  $t_{RAD}(\text{max.})$  limit, then access time is controlled by  $t_{AA}$ .

**CAPACITANCE**

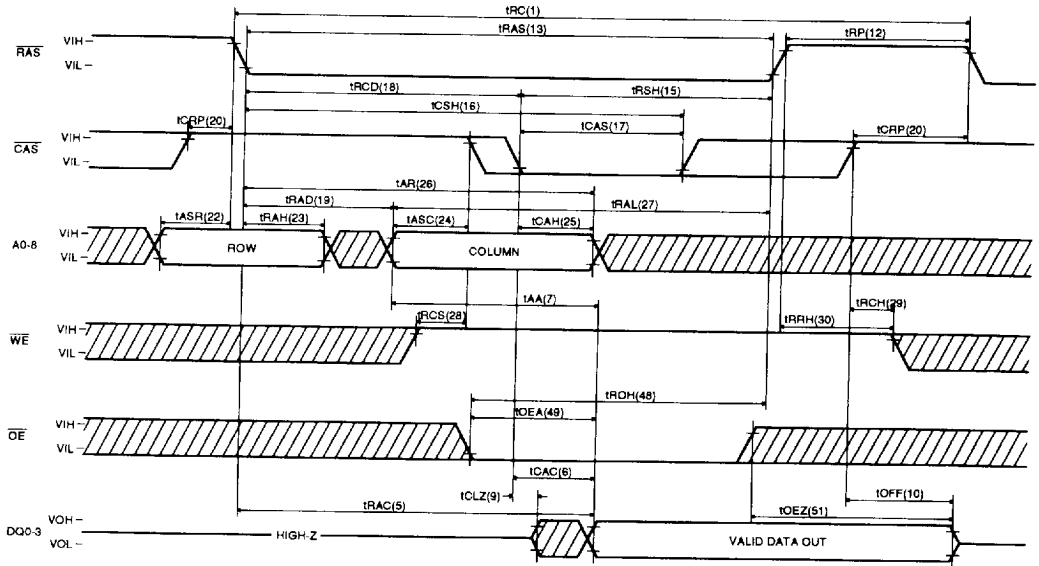
( $T_A = 25^\circ\text{C}$ ,  $V_{CC} = 5V \pm 10\%$ ,  $V_{SS} = 0V$ , unless otherwise noted.)

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
CIN1	Input Capacitance (A0-A8, D)	-	5	pF
CIN2	Input Capacitance (RAS, CAS, WE, OE)	-	7	pF
COU	Output Capacitance (Q)	-	7	pF

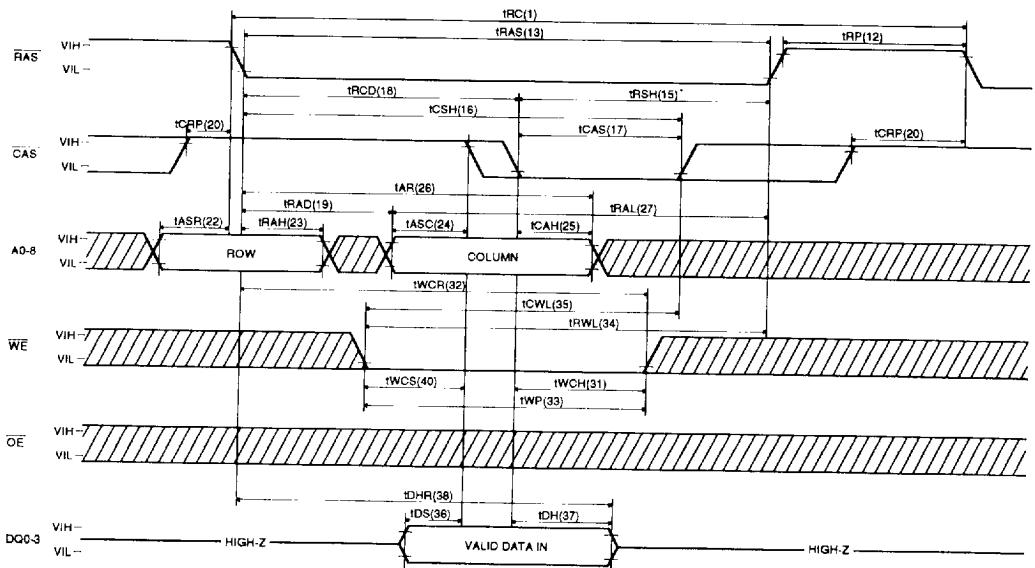


**TIMING DIAGRAM**

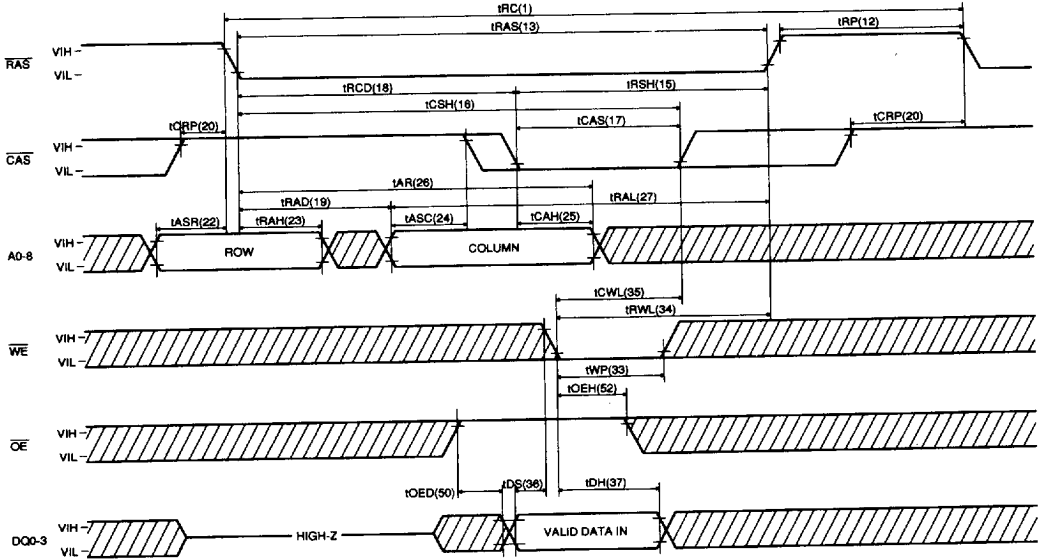
**READ CYCLE**



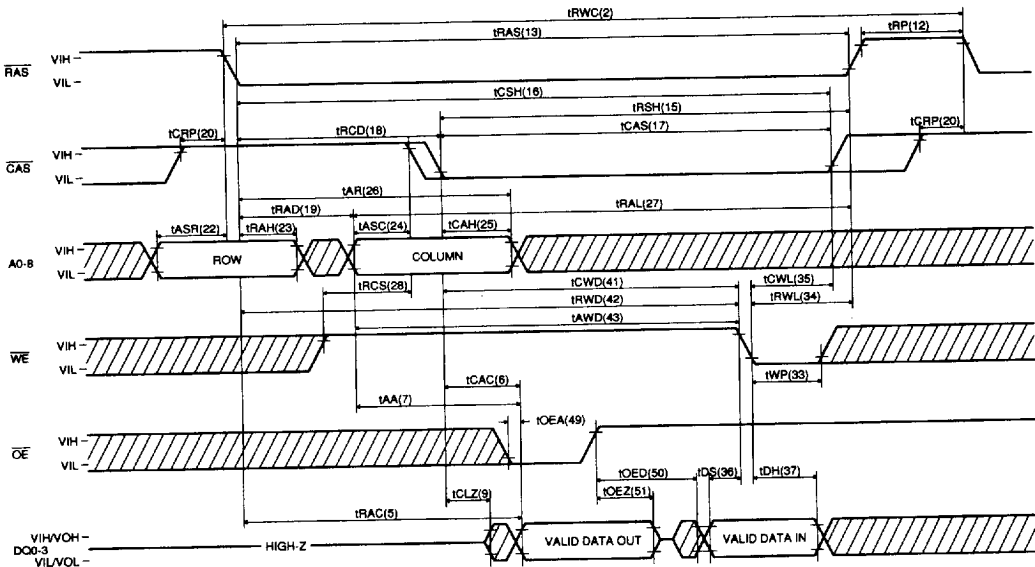
**EARLY WRITE CYCLE**



**WRITE CYCLE (OE CONTROLLED WRITE)**

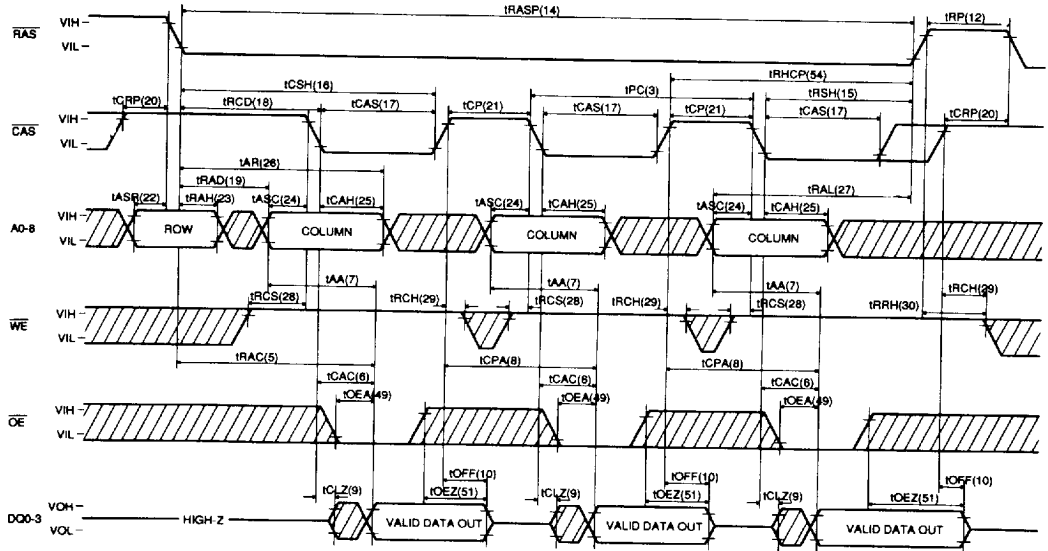


**READ-MODIFY-WRITE CYCLE**

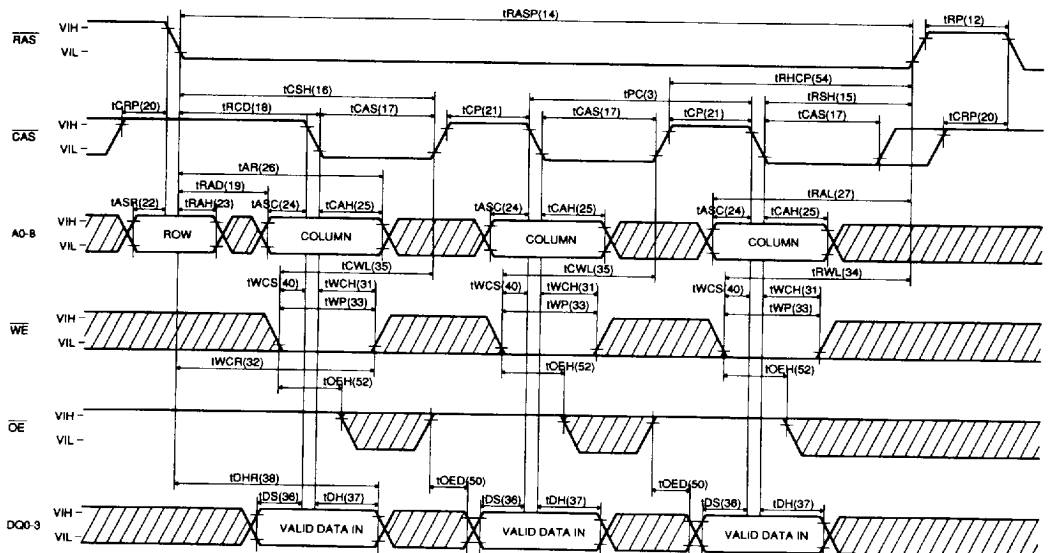




**FAST PAGE MODE READ CYCLE**

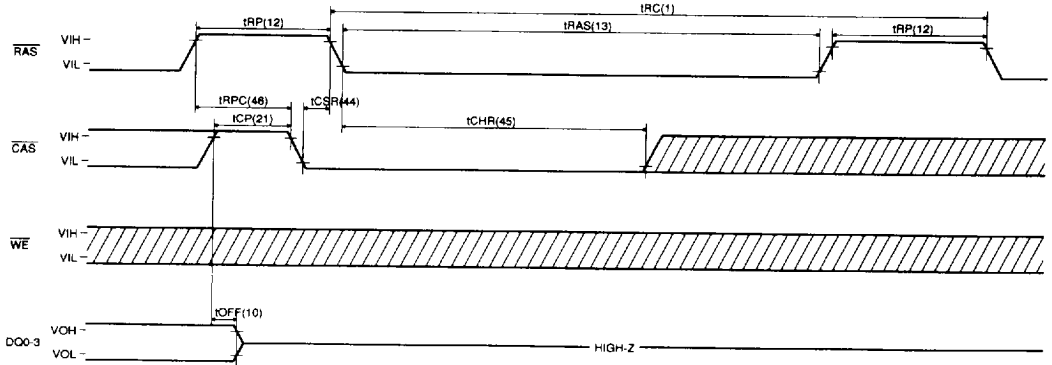


**FAST PAGE MODE EARLY WRITE CYCLE**



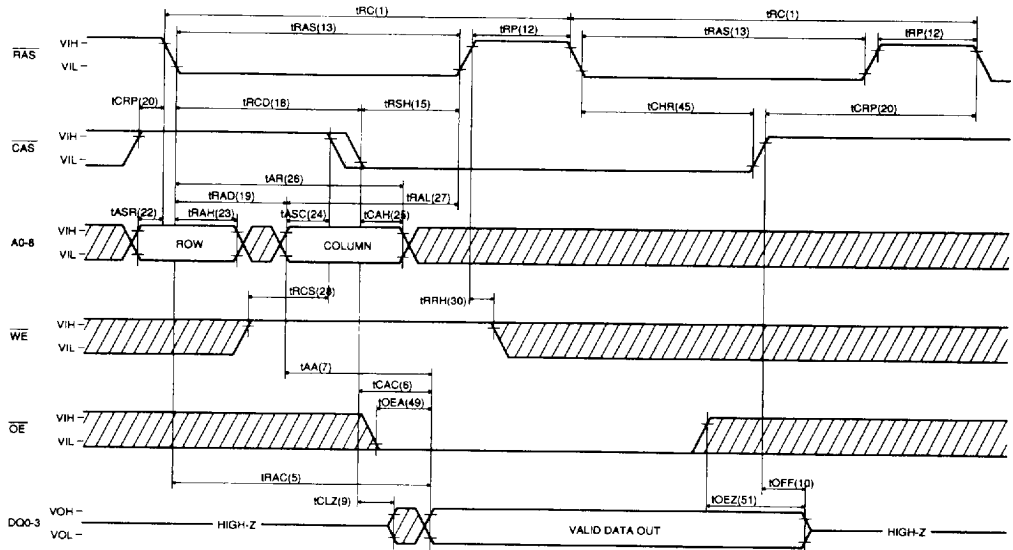


**CAS-BEFORE-RAS REFRESH CYCLE**

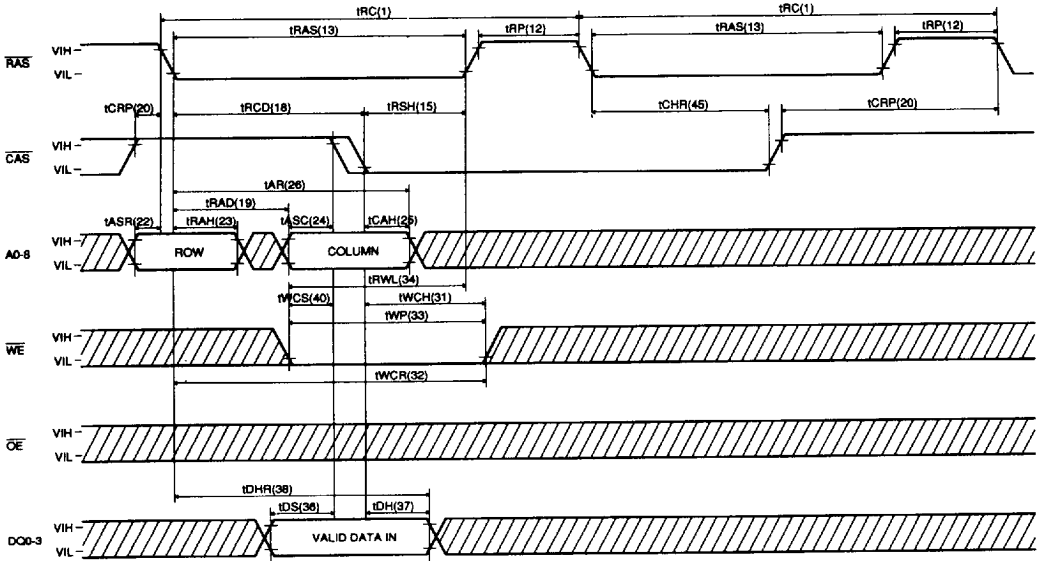


NOTE : A0-8 and OE = "H" or "L"

**HIDDEN REFRESH CYCLE (READ)**



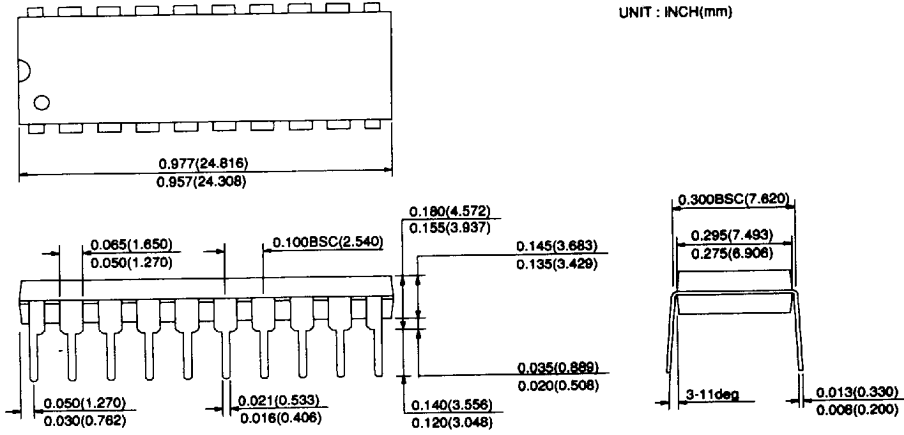
**HIDDEN REFRESH CYCLE (WRITE)**



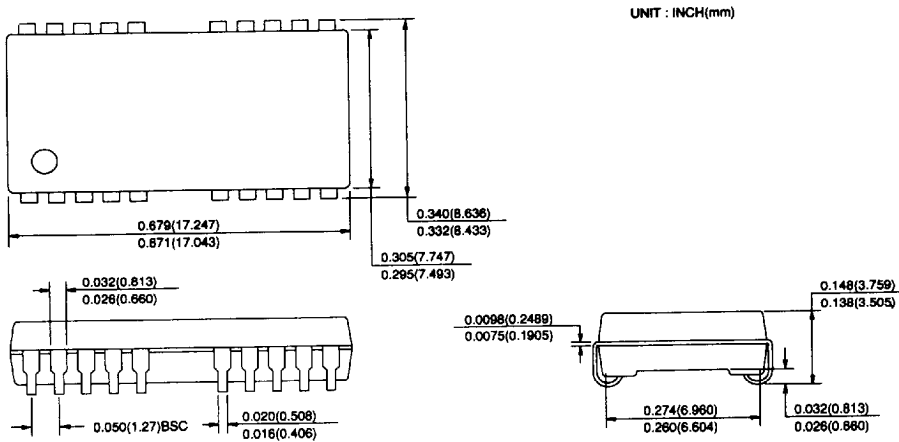


**PACKAGE INFORMATION**

**300 mil 20 pin Dual In Line Package (S)**



**300 mil 20/26 pin Thin Small Outline Package (J)**



**ORDERING INFORMATION**

PART NUMBER	SPEED	POWER	PACKAGE
HY534256S	60/70/80		PDIP
HY534256J	60/70/80		SOJ

